

Consumer SSD E1000NI Series



Introduction

Consumer SSD E1000NI adopts M.2 interface, advanced SSD control computing chip and 3D NAND flash to effectively improve R/W speed and ensure data security. E1000NI optimizes the stability and has been tested according to the standard of video surveillance server. It applies to personal computer and small-size proxy server to providing stable and high-speed service.

Available Models

HS-SSD-E1000NI

Typical Application

- PC (notebook and desktop)
- Small-size proxy sever

Features and Functions

High R/W Speed

Supports PCIe and NVMe

Max. read speed up to 1600 MB/s

3D NAND

Adopts 3D NAND flash to optimize capacity, performance and stability

Shockproof

No mechanical structure

Adopts electronic chips control

High data security

• M.2 Interface

Small and portable, easy to install





Specifications

Model		HS-SSD-E1000NI		
Capacity		256 GB	512 GB	1024 GB
Form Factor		M.2 (NGFF)		
Interface		PCle Gen 3 x 2		
Dimensions		22 mm × 80 mm × 1.5 mm (0.87" × 3.15" × 0.06")		
Drive		PCI Express Base 3.1, NVMe 1.2		
Max. sequential 128 K read speed		1500 MB/s	1600 MB/s	1600 MB/s
Max. sequential 128 K write speed		850 MB/s	1000 MB/s	1000 MB/s
Max. random 4 K read IOPS ²		170 K	230 K	230 K
Max. random 4 K write IOPS		18 0 K	180 K	180 K
Power consumption 6	Read (RMS max.)	3200 mW	3300 mW	4000 mW
	Write (RMS max.)	2800 mW	3000 mW	3300 mW
	Idle (RMS max.)	2 mW	2 mW	2 mW
Endurance (TBW)		200 TB	400 TB	800 TB
NAND flash memory		3D TLC		
Weight		≤ 20 g (0.04 lb)		
MTBF (Mean Time between Failures)		2,000,000 h		
Operation temperature		0 °C to 70 °C (32 °F to 158 °F)		
Storage temperature		-40 °C to +85 °C (-40 °F to +185 °F)		
Operation humidity		5% to 95% (no condensation)		
Limited warranty period		3 years		

^{*:} Performance test is performed in a specific testing environment. Any change of computer system, operation system, hardware, software, or functions will influence the test result.



Headquarters

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Rm.01, 21/F, F4 Building, 5th Phase-NO.1 Software Park, Guanshan 1 Rd, East Lake Development Zone, Wuhan, China(430040)

- **12**: Performance in the specifications is tested based on CrystalDiskMark.
- 3: Power consumption may differ according to flash configuration and platform. Power consumptions are measured by using CrystalDiskMark 1000 MB to test sequential R/W 5 times. Power consumptions are measured when sequential Read [1/5] to [5/5] and sequential Write [1/5] to [5/5].
- 4: The TBW value is calculated based on Workload of JEDC 218B/219A standard.
- **5**: The MTBF value is calculated based on the functional failure rate of JEDC 218B/219A standard.